

Accepted Manuscript

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PII: S0925-8388(18)33324-3

DOI: [10.1016/j.jallcom.2018.09.086](https://doi.org/10.1016/j.jallcom.2018.09.086)

Reference: JALCOM 47505

To appear in: *Journal of Alloys and Compounds*

Received Date: 14 July 2018

Revised Date: 6 September 2018

Accepted Date: 9 September 2018

Please cite this article as: X. Zhang, P. Wang, D. Qi, Y. Huang, B. Zheng, T. Lin, P. Chen, Z. Yu, J. Xu, Enhanced and wavelength-tunable near-infrared luminescence from bismuth-doped silica thin films with Au nanocrystals, *Journal of Alloys and Compounds* (2018), doi: 10.1016/j.jallcom.2018.09.086.

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Enhanced and wavelength-tunable near-infrared luminescence from bismuth-doped silica thin films with Au nanocrystals

Xiaowei Zhang^{1,2}, Pengjun Wang^{1,3}, Dongfeng Qi^{1,*}, Yanyan Huang⁴, Bolin Zheng⁵, Tao Lin⁵, Ping Chen⁵, Zhongwei Yu^{2,4}, Jun Xu²

1. Faculty of Electrical Engineering and Computer Science, Ningbo University, Ningbo, 315211, China.
2. National Laboratory of Solid State Microstructures, Department of Electronic Science and Engineering, Nanjing University, Nanjing, 210093, China.
3. College of Mathematical, Physics and Electronic Information Engineering, Wenzhou University, Wenzhou, 325035, China
4. School of Science, Nantong University, Nantong, 226000, China.
5. Department of Physical Science and Technology, Guangxi University, Nanning, 530004, China.

*E-mail: qidongfeng@nbu.edu.cn

ABSTRACT

Near-infrared (NIR) luminescence origin of Bi-doped amorphous silica thin film is elucidated by the XPS characterizations and selective photoluminescence (PL) measurements. The excitation wavelength-dependent NIR luminescence suggests the co-existence of two different types of Bi-related active centers, Bi⁰ and Bi⁺, should contribute to the NIR PL emissions at 1150 nm and 1280 nm, respectively. A confined crystallization growth strategy is designed for fabricating the uniform-size Au nanocrystals (NCs) embedded in Bi-doped amorphous silica thin film. Via controls of the doping amounts of Au ions, the NIR PL emission of Bi ions in amorphous silica thin film can be wavelength-tunable and enhanced by nearly 300% on the optimum Au ions doping amount. Temperature-dependent PL emission spectra demonstrate parts of Au ions play a role of eliminating hydroxyl groups and give rise to greatly enhanced NIR PL emission intensity. We anticipate that both the greatly enhanced and wavelength-tunable PL emission and the discussion of NIR luminescence origin will shed light on future research of Bi-doped luminescent materials.

Keywords: Thin films; Silica; Near-infrared luminescence; Sol-gel preparation

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